

YZPST-2N6075B Serise Triacs

■ Feature

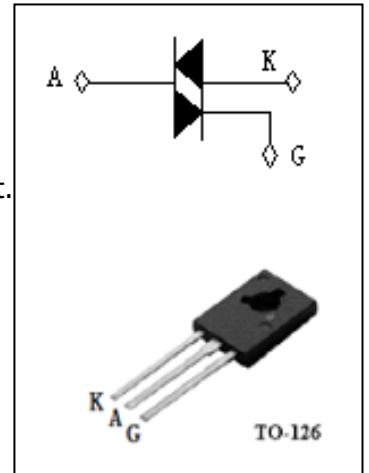
- ◆ The third quadrant sensitive trigger structure ,
The best match for commutating ability and gate sensitivity .
- ◆ Diffusion and glass passivated technology.
Ensure specification reliability and uniformity.
- ◆ Match the appropriate gate specification as high temperature requirement.

■ Main application

- ◆ Washing machine vacuum cleaner dimmer.remote switch .
- ◆ AC motor control equipment.
- ◆ Switching inductive load.

■ Outline and pin array

TO-126



■ Rate value (unless special shows , T_j=25°C)

Description	symbol	value	unit
Repetitive peak off-state voltage (T _j = -40 ~ 125°C) Half sine wave 50Hz, gate open -6075B	V _{DRM} V _{RRM}	600 600	V
Nominal RMS on-state current Full sine wave 50 Hz	I _{T(RMS)}	4	A
Non-repetitive peak surge current (junction temperature T _j =25°C) One cycle 50 Hz	I _{TSM}	30	A
Fuse current (t = 8.3 ms)	I ² _t	3.7	A ² s
Gate average power (T _c = 80°C , t = 8.3 ms)	PG(AV)	0.5	W
Gate peak current (t ≤ 2.0μ s)	I _{GM}	1	A
Work junction temperature	T _J	-40 ~ 110	°C
Storage temperature	T _{stg}	-40 ~ 150	°C

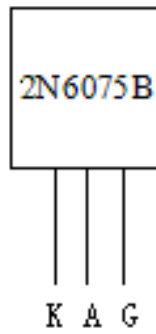
■ Thermal characteristics

Description	Symbol	Max	Unit
Thermal resistance (junction to case)	R_{jC}	3.5	$^{\circ}C/W$
Thermal resistance (junction to ambient)	R_{jA}	75	$^{\circ}C/W$

■ Electric characteristics (unless special shows $T_j=25^{\circ}C$)

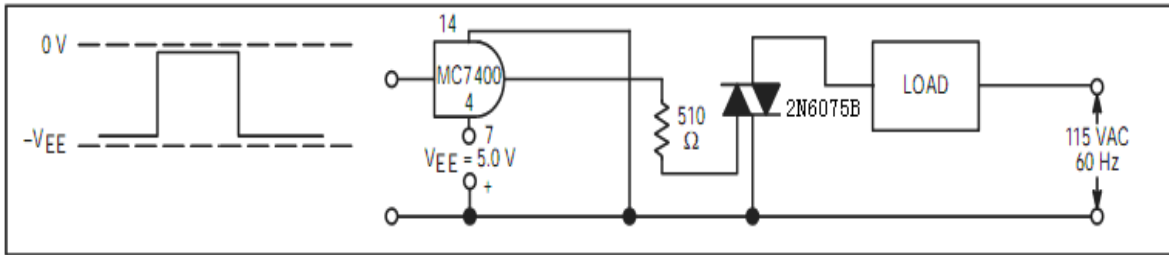
Description	Symbol	Min	Type	Max	Unit
Repetitive peak off-state current ($V_D = \text{Rated } V_{DRM}, V_{RRM}$ gate open) $T_j = 25^{\circ}C$ $T_j = 110^{\circ}C$	I_{DRM}, I_{RRM}	-	-	10 2	μA mA
Peak on-state Voltage ($I_T = 6A$)	V_T	-	-	2	V
Gate trigger current ($V_D = 12V, R_L = 30\Omega$) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+) ---B	I_{GT}	-	-	3 3 3 5	mA
Gate trigger voltage ($V_D = 12V, R_L = 30\Omega$) All series	V_{GT}	-	1.4	2.5	V
Gate non-trigger voltage ($V_D = 12V, R_L = 30\Omega, T_j = 110^{\circ}C$) All series	V_{GD}	0.2	-	-	V
Hold current (Canduction current $I_T=100mA$) $T_j = 25^{\circ}C$ $T_j = 110^{\circ}C$	I_H	-	-	15 30	mA
Critical Rate-of-Rise of Off-state Voltage $V_{DM}=1/2V_{DRM}, T_j=110^{\circ}C, R_{GK}=1K\Omega$	dv/dt	5	-		V/ μS

■ Type description

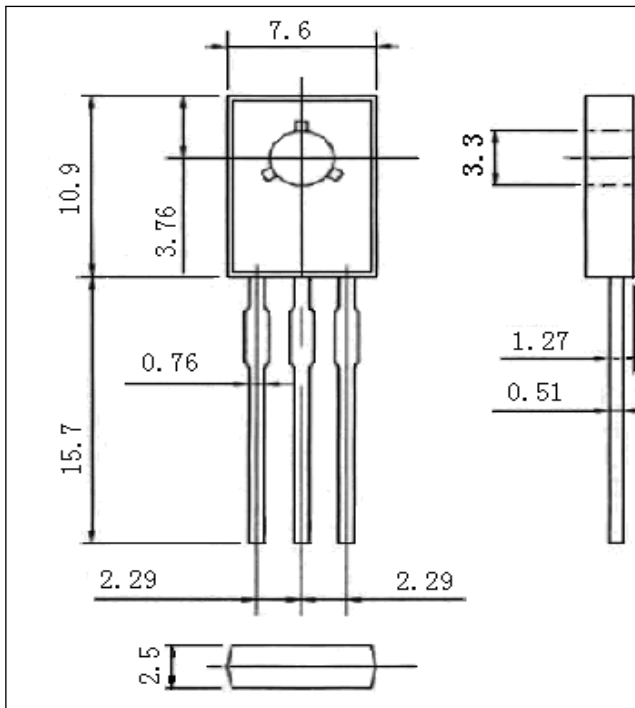


2N6075B-—Type

■ Example for typical application circuit



■ TO-126 package drawing:



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	2.500	2.900	0.098	0.114
A1	1.100	1.500	0.043	0.059
b	0.660	0.860	0.026	0.034
b1	1.170	1.370	0.046	0.054
c	0.450	0.600	0.018	0.024
D	7.400	7.800	0.291	0.307
E	10.600	11.000	0.417	0.433
e	2.290 TYP		0.090 TYP	
e1	4.480	4.680	0.176	0.184
h	0.000	0.300	0.000	0.012
L	15.300	15.700	0.602	0.618
L1	2.100	2.300	0.083	0.091
P	3.900	4.100	0.154	0.161
Φ	3.000	3.200	0.118	0.126